ABSTRACT

Fabrication of Semiconductor Devices for Light Emission

A semiconductor device for light emission having a plurality of epitaxial layers with an n-type layer for light emission and a p-type layer for light reflection. The p-type layer has at least one seed layer for an outer layer of a conductive metal. The at least at least one seed layer is a material for providing a buffer for differential thermal expansion of the outer layer and the light reflecting layer.

Figure 17(a)